



#### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max @ T <sub>A</sub> = +25°C
-30V	$2.4\Omega$ @ $V_{GS} = -10V$	-400mA
	$4\Omega @ V_{GS} = -4.5V$	-300mA

### **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

- Load Switch
- Portable Applications
- Power Management Functions

#### **Features**

- Low On-Resistance
- Ultra-Small Surfaced Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

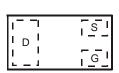
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>@4</sup>
- Weight: 0.001 grams (Approximate)



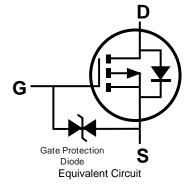




Bottom View



Top View



### **Ordering Information** (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMP32D5SFB-7B	7	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



Top View Bar Denotes Gate and Source Side

XH = Product Type Marking Code



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	-30	V	
Gate-Source Voltage		$V_{GSS}$	±25	V	
Continuous Drain Current (Note 5)	V <sub>GS</sub> = -10V	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-400 -300	mA
Continuous Drain Current (Note 6)	V <sub>GS</sub> = -10V	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-500 -400	mA
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	-1	A
Maximum Body Diode Continuous Current (Note 6)		Is	-800	mA	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Dower Discinction	(Note 5)	0	0.5	W	
Total Power Dissipation	(Note 6)	$P_{D}$	1.2		
Thermal Desigtance, Junction to Ambient	(Note 5)	-	255	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	108		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	-	V	$V_{GS} = 0V$ , $I_D = -1mA$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.3	-	-2.3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D			2.4	Ω	$V_{GS} = -10V, I_D = -200mA$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	-	_	4		$V_{GS} = -4.5V$ , $I_D = -200mA$	
Diode Forward Voltage	$V_{SD}$	-	0.8	1.2	V	$V_{GS} = 0V, I_{S} = -300mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	51	100	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	11	20	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	9	20	pF		
Total Gate Charge	Qg	-	0.62	2	nC	V <sub>GS</sub> = -4.5V	
Total Gate Charge	Qg	-	1.25	4	nC	V <sub>DS</sub> = -10V,	
Gate-Source Charge	Q <sub>gs</sub>	-	0.16	0.5	nC	$V_{GS} = -10V$ $I_{D} = -200 \text{mA}$	
Gate-Drain Charge	$Q_{gd}$	-	0.21	0.5	nC	7	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.3	10	ns	$V_{DS} = -15V, I_{D} = -500\text{mA}$ $V_{GS} = -10V, R_{G} = 1\Omega$	
Turn-On Rise Time	t <sub>R</sub>	-	7.7	15	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	31.9	60	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	17.8	40	ns		

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout. 7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.



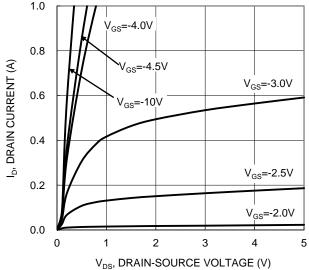


Figure 1. Typical Output Characteristic

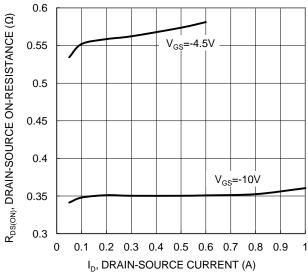


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

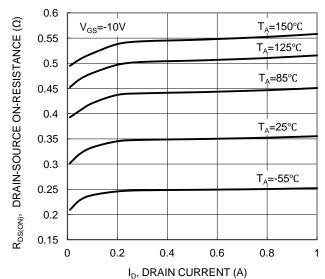
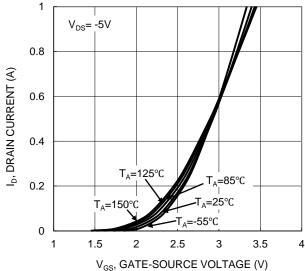
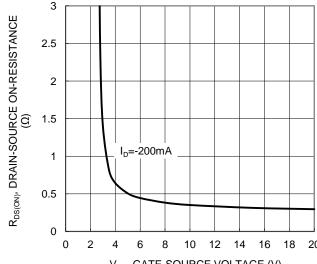


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



 $V_{\text{GS}}$ , GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

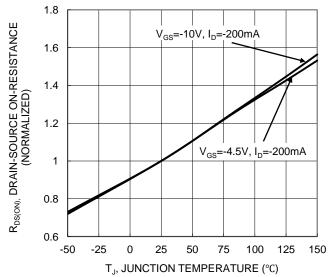


Figure 6. On-Resistance Variation with Temperature





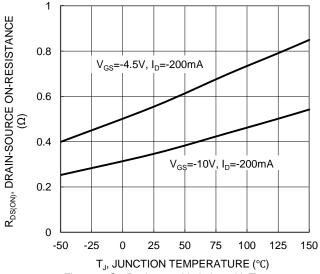
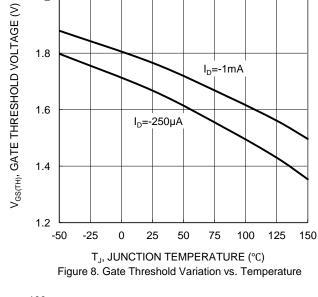


Figure 7. On-Resistance Variation with Temperature



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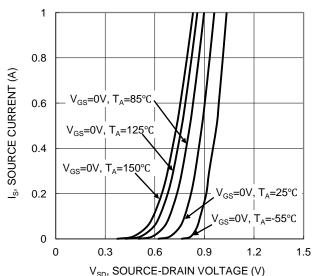
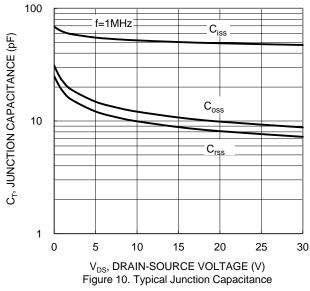
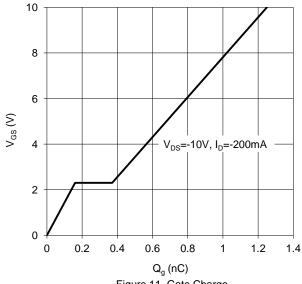
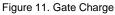


Figure 9. Diode Forward Voltage vs. Current







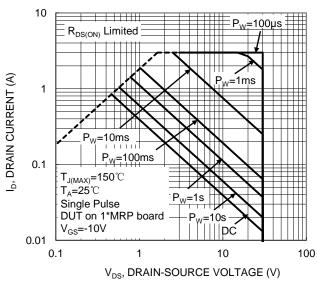
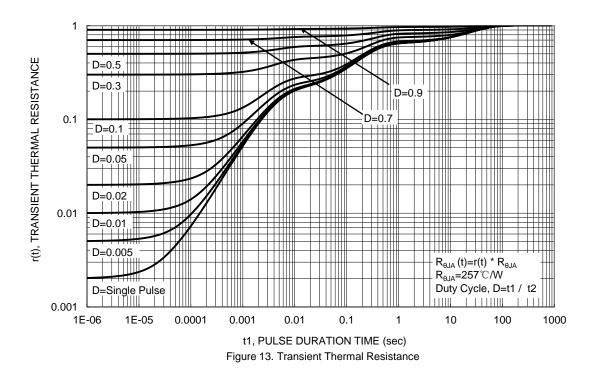


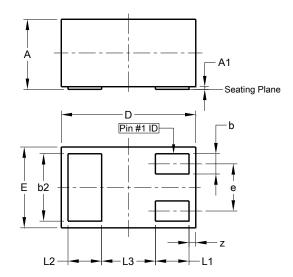
Figure 12. SOA, Safe Operation Area





# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

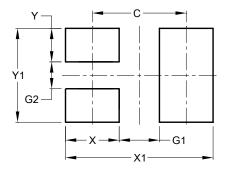


X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	ı	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
z	0.02	0.08	0.05		
All Dimensions in mm					



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70

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